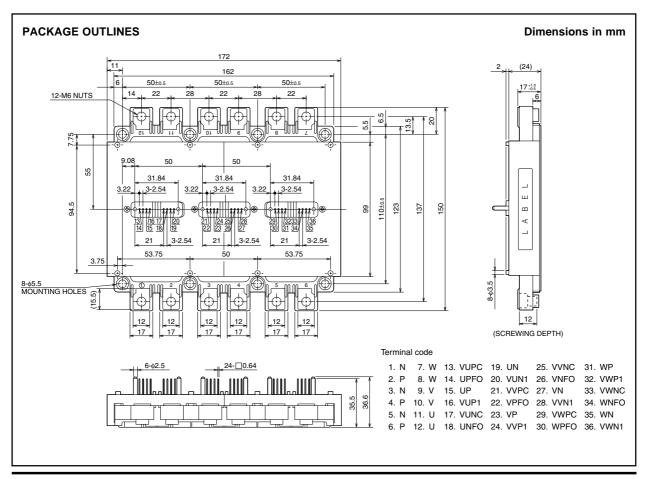
FEATURE

- a) Adopting new 5th generation IGBT (CSTBT) chip, which performance is improved by $1\mu m$ fine rule process. For example, typical Vce(sat)=1.9V @Tj=125°C
- b) I adopt the over-temperature conservation by Tj detection of CSTBT chip, and error output is possible from all each conservation upper and lower arm of IPM.
- 3 ϕ 450A, 1200V Current-sense IGBT type inverter
- · Monolithic gate drive & protection logic
- Detection, protection & status indication circuits for, shortcircuit, over-temperature & under-voltage (Fo available from all arm devices)
- Acoustic noise-less 75kW class inverter application
- UL Recognized Yellow Card No.E80276(N) File No.E80271

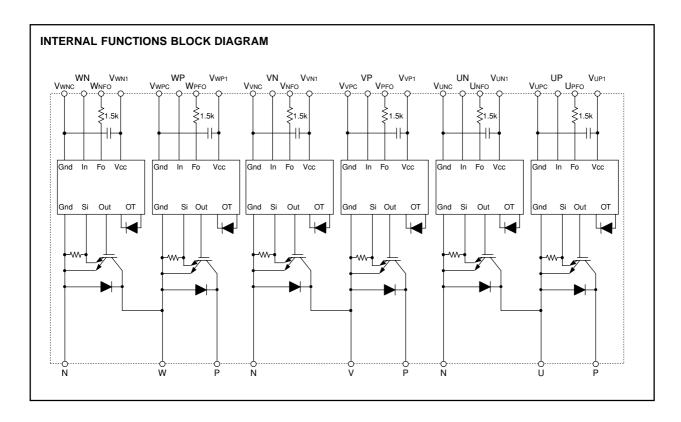
APPLICATION

General purpose inverter, servo drives and other motor controls





FLAT-BASE TYPE INSULATED PACKAGE



MAXIMUM RATINGS (Tj = 25° C, unless otherwise noted)

INVERTER PART

Symbol	Parameter	Condition	Ratings	Unit
VCES	Collector-Emitter Voltage	VD = 15V, VCIN = 15V	1200	V
±IC	Collector Current	Tc = 25°C	450	Α
±ICP	Collector Current (Peak)	Tc = 25°C	900	Α
Pc	Collector Dissipation	$Tc = 25^{\circ}C$ (Note-1)	2500	W
Tj	Junction Temperature		-20 ~ +150	°C

CONTROL PART

Symbol	Parameter	Condition	Ratings	Unit
VD	Supply Voltage	Applied between: Vup1-Vupc, Vvp1-Vvpc, Vwp1-Vwpc Vun1-Vunc, Vvn1-Vvnc, Vwn1-Vwnc	20	٧
VCIN	Input Voltage	Applied between: UP-VuPc, VP-VvPc, WP-VwPc UN-VuNc, VN-VvNc, WN-VwNc	20	V
VFO	Fault Output Supply Voltage	Applied between: UPFO-VUPC, VPFO-VVPC, WPFO-VWPC UNFO-VUNC, VNFO-VVNC, WNFO-VWNC	20	٧
IFO	Fault Output Current	Sink current at UPFO, VPFO, WPFO, UNFO, VNFO, WNFO terminals	20	mA

FLAT-BASE TYPE INSULATED PACKAGE

TOTAL SYSTEM

Symbol	Parameter	Condition	Ratings	Unit
VCC(PROT)	Supply Voltage Protected by SC	VD = 13.5 \sim 16.5V, Inverter Part, Tj = +125 $^{\circ}$ C Start	800	V
VCC(surge)	Supply Voltage (Surge)	Applied between : P-N, Surge value	1000	V
Tstg	Storage Temperature		− 40 ~ +125	°C
Viso	Isolation Voltage	60Hz, Sinusoidal, Charged part to Base, AC 1 min.	2500	Vrms

THERMAL RESISTANCES

	_	Condition		Limits			
Symbol Parameter		Condition		Тур.	Max.	Unit	
Rth(j-c)Q	Junction to case Thermal	Inverter IGBT (per 1 element) (Note-1)	_	_	0.05		
Rth(j-c)F	Resistances	Inverter FWDi (per 1 element) (Note-1)	_	_	0.09	∘c/w l	
Rth(c-f)	Contact Thermal Resistance	Case to fin, (per 1 module)		_	0.014	30/00	
		Thermal grease applied (Note-1)	-			1	

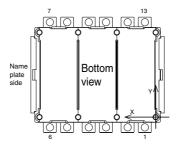
(Note-1) Tc measurement point is just under the chip.

If you use this value, Rth(f-a) should be measured just under the chips.

Table 1: Tc (under the chip) measurement point is below.

(Unit:mm)

	arm	U	Р	V	Р	W	/P	U	N	V	N	W	'N
ax	dis	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi
	X	30.1	19.2	80.1	69.2	130.1	119.2	19.8	30.7	69.8	80.7	119.8	130.7
	Υ	82.7	82.7	82.7	82.7	82.7	82.7	27.2	27.2	27.2	27.2	27.2	27.2



ELECTRICAL CHARACTERISTICS (Tj = 25° C, unless otherwise noted) **INVERTER PART**

		Condition			Unit			
Symbol	Parameter	Condit	1011		Min.	Тур.	Max.	Ullit
Vor.	Collector-Emitter	VD = 15V, IC = 450A		Tj = 25°C		1.8	2.3	V
VCE(sat)	Saturation Voltage	VCIN = 0V	(Fig. 1)	Tj = 125°C		1.9	2.4	V
VEC	FWDi Forward Voltage	-IC = 450A, VD = 15V, VCIN =	15V	(Fig. 2)		2.8	3.9	V
ton		\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\			0.5	1.0	2.5	
trr		VD = 15V, VCIN = 0V↔15V			_	0.5	0.8	
tc(on)	Switching Time	VCC = 600V, IC = 450A			_	0.4	1.0	μs
toff		Tj = 125°C	(Fir. 0. 4)	_	2.3	3.5		
tc(off)		Inductive Load		(Fig. 3, 4)	_	0.7	1.2	
la=a	Collector-Emitter	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	(F: F)	Tj = 25°C	_	_	1	
ICES	Cutoff Current	VCE = VCES, VCIN = 15V	(Fig. 5)	Tj = 125°C	_	_	10	mA

FLAT-BASE TYPE INSULATED PACKAGE

CONTROL PART

Cumphal	Danie marten	O a madiki a m			1.1		
Symbol Parameter		Condition	Condition		Тур.	Max.	Unit
ID	Circuit Current	VD = 15V. VCIN = 15V	V*N1-V*NC	_	20	27	m 1
וט	Circuit Current	VD = 13V, VCIN = 13V	V*P1-V*PC	_	20	27	mA
Vth(ON)	Input ON Threshold Voltage	Applied between: UP-VUPC, VP-VVPC,	WP-VWPC	1.2	1.5	1.8	V
Vth(OFF)	Input OFF Threshold Voltage	Un-Vunc, Vn-Vvnc, V	Wn-Vwnc	1.7	2.0	2.3	
SC	Short Circuit Trip Level	-20 ≤ Tj ≤ 125°C, VD = 15V	(Fig. 3,6)	900	-	_	Α
toff(SC)	Short Circuit Current Delay Time	VD = 15V	(Fig. 3,6)	_	0.2	_	μs
OT	Over Temperature Pretection	VD = 15V	Trip level	135	145	_	°C
OTr	Over Temperature Protection	Detect Tj of IGBT chip	Reset level	_	125	_	
UV	Supply Circuit Under-Voltage	–20 ≤ T _i ≤ 125°C	Trip level	11.5	12.0	12.5	V
UVr	Protection	-20 ≤ 1j ≤ 125 C	Reset level	_	12.5	_	\ \
IFO(H)	Fault Output Current	VD = 15V. VFO = 15V	(Note-2)	_	_	0.01	mA
IFO(L)	Fault Output Current	VD = 13V, VFO = 13V	(14016-2)	_	10	15	'''^
tFO	Minimum Fault Output Pulse Width	VD = 15V	(Note-2)	1.0	1.8	_	ms

(Note-2) Fault output is given only when the internal SC, OT & UV protections schemes of either upper or lower arm device operate to protect it.

MECHANICAL RATINGS AND CHARACTERISTICS

		Condition		Limits			Unit
Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit	
_	Mounting torque	Main terminal	screw: M6	3.5	4.0	4.5	N•m
_	Mounting torque	Mounting part	screw : M5	2.5	3.0	3.5	N•m
_	Weight	_		_	1250	_	g

RECOMMENDED CONDITIONS FOR USE

Symbol	Parameter	Condition	Recommended value	Unit
Vcc	Supply Voltage	Applied across P-N terminals	≤ 800	V
VD	Control Supply Voltage	Applied between: VuP1-VuPc, VvP1-VvPc, VwP1-VwPc VuN1-VuNc, VvN1-VvNc, VwN1-VwNc (Note-3)	15 ± 1.5	V
VCIN(ON)	Input ON Voltage	Applied between : UP-VUPC, VP-VVPC, WP-VWPC	≤ 0.8	v
VCIN(OFF)	Input OFF Voltage	Un-Vunc, Vn-Vvnc, Wn-Vwnc	≥ 9.0	
fPWM	PWM Input Frequency	Using Application Circuit of Fig. 8	≤ 20	kHz
tdead	Arm Shoot-through Blocking Time	For IPM's each input signals (Fig. 7)	≥ 3.0	μѕ

(Note-3) With ripple satisfying the following conditions: dv/dt swing $\leq \pm 5V/\mu s$, Variation $\leq 2V$ peak to peak

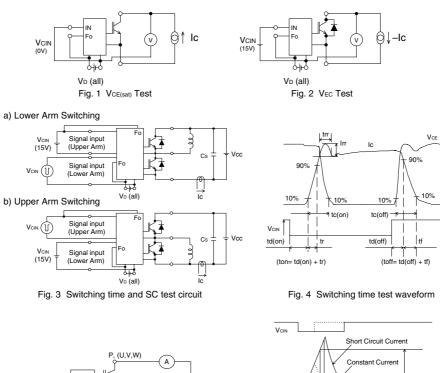


FLAT-BASE TYPE INSULATED PACKAGE

PRECAUTIONS FOR TESTING

- Before appling any control supply voltage (VD), the input terminals should be pulled up by resistores, etc. to their corresponding supply voltage and each input signal should be kept off state.
 After this, the specified ON and OFF level setting for each input signal should be done.
- 2. When performing "SC" tests, the turn-off surge voltage spike at the corresponding protection operation should not be allowed to rise above VCEs rating of the device.

(These test should not be done by using a curve tracer or its equivalent.)



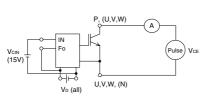


Fig. 5 Ices Test

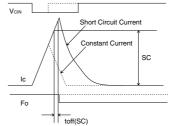
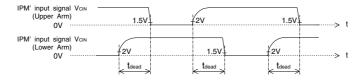


Fig. 6 SC test waveform



1.5V: Input on threshold voltage Vth(on) typical value, 2V: Input off threshold voltage Vth(off) typical value

Fig. 7 Dead time measurement point example



FLAT-BASE TYPE INSULATED PACKAGE

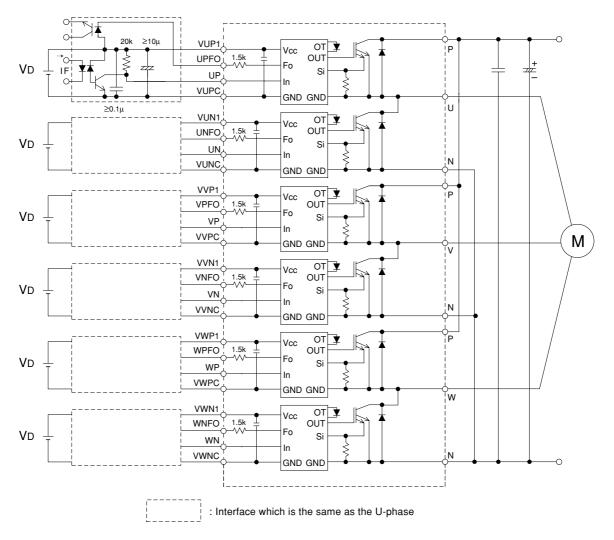


Fig. 8 Application Example Circuit

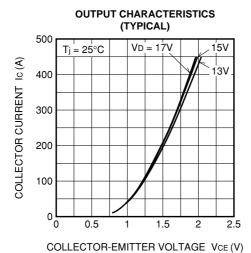
NOTES FOR STABLE AND SAFE OPERATION;

- Design the PCB pattern to minimize wiring length between opto-coupler and IPM's input terminal, and also to minimize the stray capacity between the input and output wirings of opto-coupler.
- Connect low impedance capacitor between the Vcc and GND terminal of each fast switching opto-coupler.
- Fast switching opto-couplers: tPLH, tPHL ≤ 0.8μs, Use High CMR type.
- Slow switching opto-coupler: CTR > 100%
- Use 6 isolated control power supplies (VD). Also, care should be taken to minimize the instantaneous voltage charge of the power supply.
- Make inductance of DC bus line as small as possible, and minimize surge voltage using snubber capacitor between P and N terminal.
- Use line noise filter capacitor (ex. 4.7nF) between each input AC line and ground to reject common-mode noise from AC line and improve noise immunity of the system.

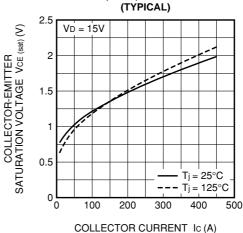


FLAT-BASE TYPE INSULATED PACKAGE

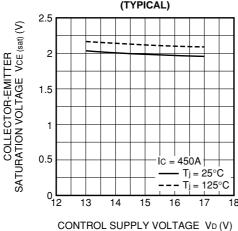
PERFORMANCE CURVES



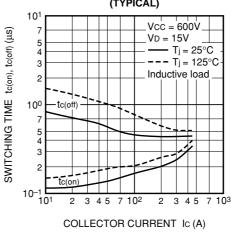
COLLECTOR-EMITTER SATURATION VOLTAGE (VS. Ic) CHARACTERISTICS



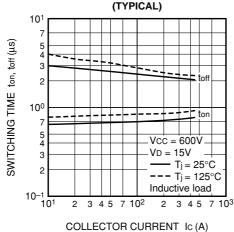
COLLECTOR-EMITTER SATURATION VOLTAGE (VS. VD) CHARACTERISTICS (TYPICAL)



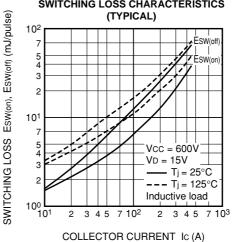
SWITCHING TIME CHARACTERISTICS (TYPICAL)



SWITCHING TIME CHARACTERISTICS (TYPICAL)

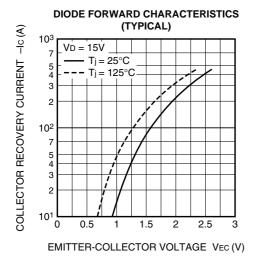


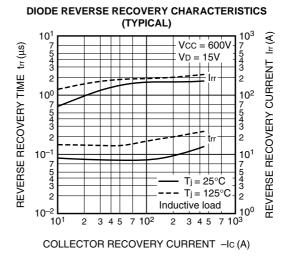
SWITCHING LOSS CHARACTERISTICS

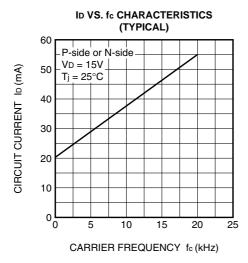


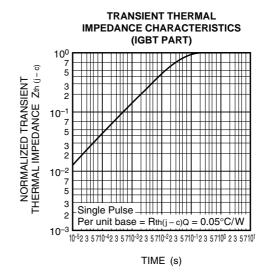


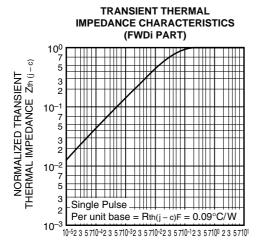
FLAT-BASE TYPE INSULATED PACKAGE











TIME (s)

Important Notice

The information contained in this datasheet shall in no event be regarded as a guarantee of conditions or characteristics. This product has to be used within its specified maximum ratings, and is subject to customer's compliance with any applicable legal requirement, norms and standards.

Except as otherwise explicitly approved by Mitsubishi Electric Corporation in a written document signed by authorized representatives of Mitsubishi Electric Corporation, our products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.

In usage of power semiconductor, there is always the possibility that trouble may occur with them by the reliability lifetime such as Power Cycle, Thermal Cycle or others, or when used under special circumstances (e.g. condensation, high humidity, dusty, salty, highlands, environment with lots of organic matter / corrosive gas / explosive gas, or situations which terminals of semiconductor products receive strong mechanical stress). Therefore, please pay sufficient attention to such circumstances. Further, depending on the technical requirements, our semiconductor products may contain environmental regulation substances, etc. If there is necessity of detailed confirmation, please contact our nearest sales branch or distributor.

The contents or data contained in this datasheet are exclusively intended for technically trained staff. Customer's technical departments should take responsibility to evaluate the suitability of Mitsubishi Electric Corporation product for the intended application and the completeness of the product data with respect to such application. In the customer's research and development, please evaluate it not only with a single semiconductor product but also in the entire system, and judge whether it's applicable. As required, pay close attention to the safety design by installing appropriate fuse or circuit breaker between a power supply and semiconductor products to prevent secondary damage. Please also pay attention to the application note and the related technical information.

Keep safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

- •These materials are intended as a reference to assist our customers in the selection of the Mitsubishi Electric Semiconductor product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Mitsubishi Electric Corporation or a third party.
- •Mitsubishi Electric Corporation assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
- •All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Mitsubishi Electric Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact Mitsubishi Electric Corporation or an authorized Mitsubishi Electric Semiconductor product distributor for the latest product information before purchasing a product listed herein.

The information described here may contain technical inaccuracies or typographical errors. Mitsubishi Electric Corporation assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.

Please also pay attention to information published by Mitsubishi Electric Corporation by various means, including the Mitsubishi Electric Semiconductor home page (http://www.MitsubishiElectric.com/semiconductors/).

- •When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Mitsubishi Electric Corporation assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.
- •Mitsubishi Electric Corporation semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Electric Semiconductor product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
- •The prior written approval of Mitsubishi Electric Corporation is necessary to reprint or reproduce in whole or in part these materials.
- •If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.
- Any diversion or re-export contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.
- •Please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Electric Semiconductor product distributor for further details on these materials or the products contained therein.

Generally the listed company name and the brand name are the trademarks or registered trademarks of the respective companies.